

## PATENT ABSTRACTS OF JAPAN

(11)Publication number:

53-028374

(43) Date of publication of application: 16.03.1978

(51)Int.CI.

H01L 21/205

B01J 17/26

H01L 21/86

(21)Application number : 51-102670

(71)Applicant: HITACHI LTD

(22) Date of filing:

30.08.1976

(72)Inventor: IIDA SHINYA

KOMATSU HIDEO MIZUTANI TATSUMI ISHII MITSURU

## (54) WAFER PRODUCTION

(57) Abstract:

PURPOSE: To reduce the warpage of wafers by growing single crystal or polycrystalline Si also only the back surface of a sapphire single crystal wafer.

## LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]

Best Available Copy



Copyright (C); 1998,2003 Japan Patent Office

## Best Available Copy